

Data sheet acquired from Harris Semiconductor SCHS273A

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Features

- Buffered Inputs
- Typical Propagation Delay: 8ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^{\circ}C$
- Fanout (Over Temperature Range)
 - Standard Outputs..... 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, II \leq 1µA at VOL, VOH

CD54/74HC11, CD54/74HCT11

High Speed CMOS Logic Triple 3-Input AND Gate

Description

The 'HC11 and 'HCT11 logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The HCT logic family is functionally pin compatible with the standard LS logic family.

Ordering Information

PART NUMBER	TEMP. RANGE (^o C)	PACKAGE
CD54HC11F	-55 to 125	14 Ld CERDIP
CD54HC11F3A	-55 to 125	14 Ld CERDIP
CD74HC11E	-55 to 125	14 Ld PDIP
CD74HC11M	-55 to 125	14 Ld SOIC
CD54HCT11F	-55 to 125	14 Ld CERDIP
CD54HCT11F3A	-55 to 125	14 Ld CERDIP
CD74HCT11E	-55 to 125	14 Ld PDIP
CD74HCT11M	-55 to 125	14 Ld SOIC

NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Die for this part number is available which meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

Pinout



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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Functional Diagram



TRUTH TABLE

INP	UTS		OUTPUT
nA	nB	nC	nY
L	L	L	L
L	L	Н	L
L	н	L	L
L	н	н	L
н	L	L	L
н	L	н	L
Н	Н	L	L
Н	Н	Н	Н

Logic Symbol



Absolute Maximum Ratings

DC Supply Voltage, V _{CC}
DC Input Diode Current, I _{IK}
For $V_{I} < -0.5V$ or $V_{I} > V_{CC} + 0.5V$
DC Output Diode Current, IOK
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ ±20mA
DC Output Source or Sink Current per Output Pin, IO
For $V_{O} > -0.5V$ or $V_{O} < V_{CC} + 0.5V$
DC V _{CC} or Ground Current, I _{CC or} I _{GND} ±50mA
Operating Conditions

Temperature Range (T _A)55 ^o C to 125 ^o C
Supply Voltage Range, V _{CC}
HC Types
HCT Types4.5V to 5.5V
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

Thermal Information

Thermal Resistance (Typical, Note 3)	θ _{JA} (^o C/W)	θ _{JC} (^o C/W)
PDIP Package	100	N/A
CERDIP Package	130	55
SOIC Package	180	N/A
Maximum Junction Temperature (Hermetic	Package or Di	e) 175 ⁰ C
Maximum Junction Temperature (Plastic F	Package)	150 ⁰ C
Maximum Storage Temperature Range	65	^o C to 150 ^o C
Maximum Lead Temperature (Soldering 1	0s)	300 ⁰ C
(SOIC - Lead Tips Only)		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

		TEST CONDITIONS			25 ⁰ C			-40 ⁰ C TO 85 ⁰ C		-55°C TO 125°C										
PARAMETER S	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS								
HC TYPES	-								-	-	-	-								
High Level Input	VIH	-	-	2	1.5	-	-	1.5	-	1.5	-	V								
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V								
				6	4.2	-	-	4.2	-	4.2	-	V								
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V								
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V								
				6	-	-	1.8	-	1.8	-	1.8	V								
High Level Output	V _{OH}	V _{IH} or	-0.02	2	1.9	-	-	1.9	-	1.9	-	V								
Voltage CMOS Loads		VIL	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V								
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V								
High Level Output	1										-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V								
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V								
Low Level Output	V _{OL}	V _{IH} or	0.02	2	-	-	0.1	-	0.1	-	0.1	V								
Voltage		VIL	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V								
			0.02	6	-	-	0.1	-	0.1	-	0.1	V								
Low Level Output	1		-	-	-	-	-	-	-	-	-	V								
Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V								
			5.2	6	-	-	0.26	-	0.33	-	0.4	V								
Input Leakage Current	lı	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA								

DC Electrical Specifications (Continued)

		TEST CONDITIONS			25 ⁰ C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	ТҮР	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	2	-	20	-	40	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V _{CC} and GND	-	5.5	-		±0.1	-	±1	-	±1	μΑ
Quiescent Device Current	Icc	V _{CC} or GND	-	5.5	-	-	2	-	20	-	40	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI _{CC}	V _{CC} - 2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

4. For dual-supply systems theorectical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
All	0.5

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. $360\mu A$ max at $25^{\circ}C$.

Switching Specifications Input t_r, t_f = 6ns

		TEST	TEST	TEST			25 ⁰ C		-40 ⁰ C T	O 85°C	-55°C T	O 125ºC	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	ТҮР	MAX	MIN	MAX	MIN	MAX	UNITS		
HC TYPES													
Propagation Delay, Input to Output (Figure 1)	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	100	-	125	-	150	ns		
			4.5	-	-	20	-	25	-	30	ns		
			6	-	-	17	-	21	-	26	ns		
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	8	-	-	-	-	-	ns		

		TEST	v _{cc}	25 ⁰ C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	ТҮР	MAX	MIN	MAX	MIN	MAX	UNITS
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	Cl	C _L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	C _L = 15pF	5	-	26	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	-	28	-	35	-	42	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	11	-	-	-	-	-	ns
Transition Times (Figure 2)	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	Cl	C _L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	-	28	-	-	-	-	-	pF

Switching Specifications Input tr. tr = 6ns (Continued)

NOTES:

5. C_{PD} is used to determine the dynamic power consumption, per gate. 6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms







FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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